

FQP11N40C / FQPF11N40C

N-Channel QFET® MOSFET

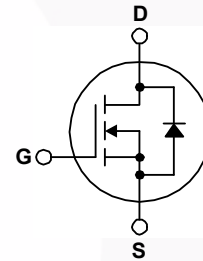
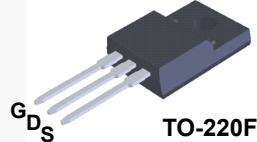
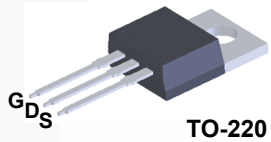
400 V, 10.5 A, 530 mΩ

Features

- 10.5 A, 400 V, $R_{DS(on)} = 530 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 5.25 \text{ A}$
- Low Gate Charge (Typ. 28 nC)
- Low Crss (Typ. 85 pF)
- 100% Avalanche Tested

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQP11N40C	FQPF11N40C	Unit
V_{DSS}	Drain to Source Voltage	400		V
I_D	Drain Current	-Continuous ($T_C = 25^\circ\text{C}$)	10.5	10.5 *
		-Continuous ($T_C = 100^\circ\text{C}$)	6.6	6.6 *
I_{DM}	Drain Current - Pulsed (Note 1)	42	42 *	A
V_{GSS}	Gate to Source Voltage	± 30		V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	360		mJ
I_{AR}	Avalanche Current (Note 1)	11		A
E_{AR}	Repetitive Avalanche Energy (Note 1)	13.5		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	135	44	W
		1.07	0.35	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300		$^\circ\text{C}$

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FQP11N40C	FQPF11N40C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.93	2.86	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max	62.5	62.5	$^\circ\text{C}/\text{W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQP11N40C	FQP11N40C	TO-220	Tube	N/A	50 units
FQPF11N40C	FQPF11N40C	TO-220F	Tube	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	400	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.54	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 320\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 5.25\text{ A}$	--	0.43	0.53	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 5.25\text{ A}$	--	7.1	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	--	840	1090	pF
C_{oss}	Output Capacitance		--	250	325	pF
C_{rss}	Reverse Transfer Capacitance		--	85	110	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 200\text{ V}, I_D = 10.5\text{ A}, R_G = 25\ \Omega$ (Note 4)	--	14	40	ns
t_r	Turn-On Rise Time		--	89	190	ns
$t_{d(off)}$	Turn-Off Delay Time		--	81	170	ns
t_f	Turn-Off Fall Time		--	81	170	ns
Q_g	Total Gate Charge	$V_{DS} = 320\text{ V}, I_D = 10.5\text{ A}, V_{GS} = 10\text{ V}$ (Note 4)	--	28	35	nC
Q_{gs}	Gate-Source Charge		--	4	--	nC
Q_{gd}	Gate-Drain Charge		--	15	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	10.5	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	42	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 10.5\text{ A}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 10.5\text{ A}, di_F / dt = 100\text{ A}/\mu\text{s}$	--	290	--	ns
Q_{rr}	Reverse Recovery Charge		--	2.4	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. $L = 5.7\text{ mH}, I_{AS} = 10.5\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 10.5\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

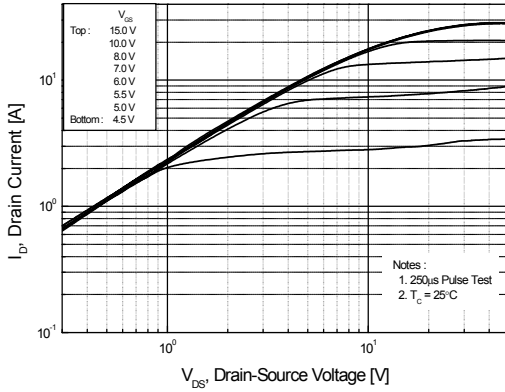


Figure 2. Transfer Characteristics

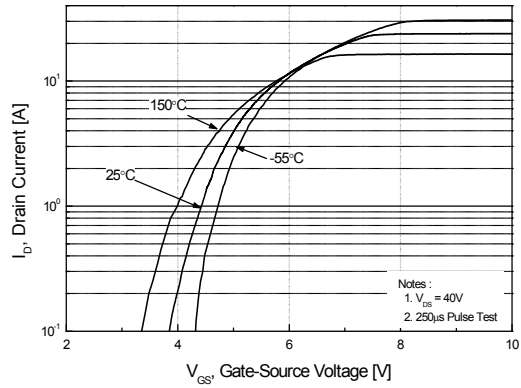


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

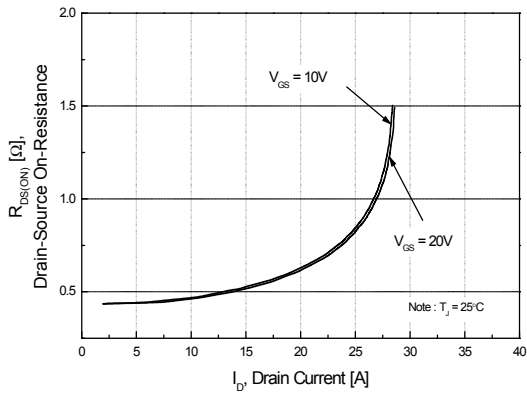


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

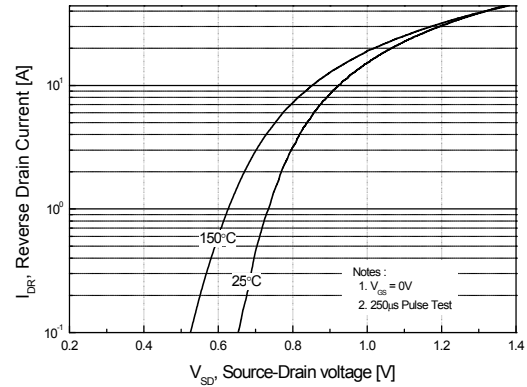


Figure 5. Capacitance Characteristics

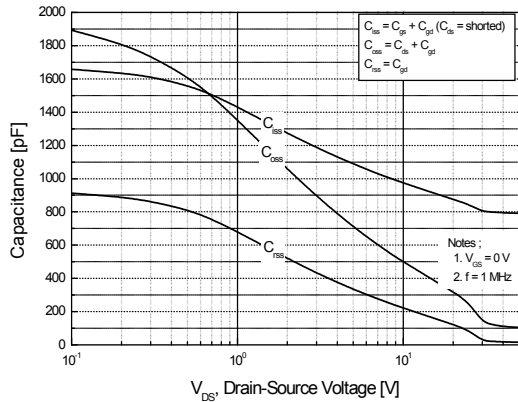


Figure 6. Gate Charge Characteristics

